

Title (en)

ELECTRONIC SEMICONDUCTOR COMPONENT, AND PROCESS FOR MANUFACTURING A PRETREATED COMPOSITE SUBSTRATE FOR AN ELECTRONIC SEMICONDUCTOR COMPONENT

Title (de)

ELEKTRONISCHES HALBLEITERBAUELEMENT UND VERFAHREN ZUR HERSTELLUNG EINES VORBEHANDELTEN VERBUNDSUBSTRATS FÜR EIN ELEKTRONISCHES HALBLEITERBAUELEMENT

Title (fr)

COMPOSANT SEMI-CONDUCTEUR ÉLECTRONIQUE ET PROCÉDÉ DE FABRICATION D'UN SUBSTRAT COMPOSITE PRÉTRAITÉ POUR COMPOSANT SEMI-CONDUCTEUR ÉLECTRONIQUE

Publication

EP 4264672 A1 20231025 (DE)

Application

EP 21836128 A 20211210

Priority

- DE 102020134222 A 20201218
- DE 102021109690 A 20210416
- EP 2021085296 W 20211210

Abstract (en)

[origin: WO2022128818A1] The electronic semiconductor component (50) includes a crystal (53) made of monocrystalline SiC, wherein the orientation of at least some subareas of a first surface (58) of the SiC crystal (53) extends substantially in a direction running perpendicularly to the c direction (c) of the crystal structure of the crystal (53). Also disclosed is a manufacturing process.

IPC 8 full level

H01L 29/16 (2006.01); **H01L 21/02** (2006.01); **H01L 21/18** (2006.01); **H01L 29/04** (2006.01)

CPC (source: EP US)

H01L 21/02002 (2013.01 - EP); **H01L 21/046** (2013.01 - EP); **H01L 21/0465** (2013.01 - US); **H01L 21/187** (2013.01 - EP); **H01L 29/045** (2013.01 - EP US); **H01L 29/1608** (2013.01 - EP US)

Citation (search report)

See references of WO 2022128818A1

Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)

BA ME

Designated validation state (EPC)

KH MA MD TN

DOCDB simple family (publication)

WO 2022128818 A1 20220623; EP 4264672 A1 20231025; JP 2023553477 A 20231221; US 2024055472 A1 20240215

DOCDB simple family (application)

EP 2021085296 W 20211210; EP 21836128 A 20211210; JP 2023535862 A 20211210; US 202118267872 A 20211210